Details of High Purity Materials and Single crystal wafers

Note 1: Please note that wherever the wires/foils are not available in the below-mentioned items, the other available forms should be quoted. If any of the materials is available ONLY in the powder form then it should be quoted for 100 gm. of each. However, if 100 gm. pack is not available, higher weights should be quoted as per the availability. Please quote all options.

Note 2: For all the single crystalline wafers and substrates (mentioned below), purity should be 99.999% or above. If the desired dimensions and quality are not available, the closest ones should be quoted. If any bulk rates available, they may be quoted.

S. No	Details of the material	Purity	Quantity
1	High purity materials: in form of wire (diameter: 1 - 2mm) or foil: Au (gold), Ag (silver), Ni (nickel), Cu (copper), ^{56}Fe (iron), ^{57}Fe (iron isotope), Pt (platinum), W (tungsten), Mo (Molybdenum), Ta (tantalum), Sn (tin), Cr (chromium), Zr (Zirconium), Bi (bismuth), Mn (Manganeese), Ge (germanium), Ga (metal)	99.99% or above	Each material 10 – 200 grams (Price to be quoted for different slabs of weight) (Please see note 1)
2	High purity materials in fine powder/ 1 mm or rod form : Erbium Hydride, Lithium Hydride, Calcium Hydride, Iron Phosphide, Iron Sulphide, Silver Iodide, Cesium Iodide, Silver Chloride, Calcium Fluoride, Carbon Nitride, Boron Nitride, Zinc Oxide, Potassium Bromide, Manganese Hydride, Cadmium Solphate (Merck make): 300 gm Decaboron ($B_{10}H_{14}$). Enriched Lithium (^{6}Li), Iron ^{57}Fe, ^{56}Fe Co, Ni, Sn, Sb, Au, Mn, , V, Bi, Ge, Pt, Cr, Graphite, BeO, B, Ag, In, Pb, Silver paste and Thinner Powder forms: Zn, Se, Sb, Bi, Tin (Sn), Cd SiO_2 Seleno Urea Polymers: PMMA (Quote for various molecular weights) PS (various molecular weight) LaO, Lanthanum Oxide, 99.99 or better, 20gms. $BaCO_3$, Barium carbonate 99.99 or better, 25 gms. $CaCO_3$, Calcium Carbonate 99.99 or better, 25 gms. $SrCO_3$, Strontium Carbonate 99.99 or better, 25 gms. Pr_2O_3, Praseodimium Oxide, 99.99 or better, 10 gms. Mn_3O, Manganese Oxide, 99.99 or better, 10 gms. TiO, Titanium Oxide, 99.99 or better, 10 gms. PbO_2, Lead Oxide, 99.99 or better, 10 gms.	99% and above 99.99% or above > 99.99	Pack size: 10 gm, 20 gm, 50 gm and 100 gm, 200 gm, 500gm 500 gm paste & thinner accordingly 300 – 400 gm each 100 gm 10 gm 20 – 30 gm 25 – 30 gm 25 – 30 gm 25 – 30 gm 10 – 15 gm 10 – 15 gm 20 – 25 gm 10 – 15 gm 30 – 35 gm 30 – 35 gm

	BiO, Bismuth Oxide, 99.99 or better, 20gms. CuO, Copper Oxide, 99.99 or better, 20gms.		
3	High purity and single crystalline wafers: For (a) – (k) to 2 - 4" diameter with 0.4 – 0.5 mm thickness; One-side polished (a) P-Si<100>; resistivity: 0.01-0.05 -cm (b) P-Si<100>; resistivity: 1- 15 -cm (c) P-Si<100> resistivity: 50-100 -cm (d) N-Si<100> resistivity : 0.01-0.05 -cm (e) P-Si<111>]resistivity: 0.01-0.05 -cm (f) N-Si<111> resistivity: 0.01-0.05 -cm (g) P-Si<110>; resistivity: 0.01-0.5 -cm (h) N-Si<110>; resistivity: 0.01-0.1 -cm (i) N-Si<100> CZ grown, resistivity 3 – 4 -cm (j) P-Si<100> CZ grown, resistivity 3 – 4 -cm (k) N-Si<101> CZ grown, resistivity 3 – 4 -cm (l) P-Si<111> CZ grown, resistivity 3 – 4 -cm (m) P-Ge <100> resistivity : 0.1-5 -cm (n) P-Ge <111> resistivity : 0.01-0.5 -cm (o) N-Ge <111> resistivity : 0.01 – 0.5 -cm (p) P-GaSb<100> resistivity: 0.5-5 -cm (q) Single crystalline ZnO (thickness: 0.5mm to 1mm): 1x1 in^2 (r) Al_2O_3 (sapphire) (thickness: 0.3 to 1mm)<0001>: 1x1 in^2 (s) Single crystalline SiO_2 (thickness: 0.5mm to 1mm) : 1x1 in^2 (t) Highly Oriented Pyrolitic Graphite (HOPG) (0001) (u) InP, Fe doped, <100>, Resistivity: $2x10^7$ -cm (v) InP, undoped, <100>, Resistivity: Very high (w) MgO, Orientation-(100), Resitivity: High (x) P-GaAs <100>, Zn doped, Resistivity: $1x10^7$ -cm	99.999% or above	2 - 4" diameter with 0.1 – 0.5 mm thickness (a) 150 – 200 wafers (b) 20 – 30 wafers (c) 20 – 30 wafers (d) 50 – 75 wafers (e) 75 – 100 wafers (f) 50 – 75 wafers (g) 50 – 75 wafers (h) 5 – 10 wafers (i) 15 wafers (j) 15 wafers (k) 15 wafers (l) 10 wafers (m) 30-40 wafers (n) 5 – 10 wafers (o) 5 – 10 wafers (p) 25 – 35 wafers (q) 40 – 50 wafers (r) 40 – 50 wafers (s) 40 – 50 wafers (t) 20 – 30 wafers (u) 5 – 10 wafers (v) 5 – 10 wafers (w) 10 – 15 wafers (x) 10 – 15 wafers
	(1) Ni, Length-2mm, Oriented (100), Single crystals (2) Au, Length-1mm, Oriented (100), Single crystals (3) Cu, Length-2mm, Oriented (100), Single crystals (4) NiO, Length-2mm, Single crystals	99.9999 or better	Length 1 – 2 mm 1 or 2 1 or 2

	(5) Au (111) single crystal (3 mm more) 3mm or (6) Ag (111) single crystal (3 mm more) 3 mm or		